

ABSTRACT OF THE DISCLOSUREPROCESS FOR FABRICATING A STRUCTURE OF SEMICONDUCTOR-  
ON-INSULATOR TYPE, IN PARTICULAR SiCOI

Process for fabricating a structure comprising a carrier substrate (20) and a layer of semiconductor material (12) on one surface of the carrier substrate, the process comprising the following steps:

- 5 a) forming a layer of semiconductor material (12) on one surface of a first substrate (10),
- Sub A3 b) forming a cleavage zone in the first substrate, which delimits a superficial layer (18),
- 10 c) transferring the first substrate (10), with the layer of semiconductor material (12), onto the carrier substrate (20),
- d) providing energy to cause cleavage of the first substrate along the cleavage zone (16),
- 15 e) removing said superficial layer (18) to uncover the layer of semiconductor material (12).

Figure 5.